



High power cycling capability
Low on-state and switching losses
Designed for traction and industrial applications

Phase Control Thyristor Type T253-1000-18

Maximum allowable mean on-state current				I_{TAV}	1000 A			
Repetitive peak off-state voltage				V_{DRM}	1000...1800 V			
Repetitive peak reverse voltage				V_{RRM}				
Turn-off time				t_q	200, 250, 320, 400, 500 μ s			
V_{DRM}, V_{RRM}, V	1000	1100	1200	1300	1400	1500	1600	1800
Voltage code	10	11	12	13	14	15	16	18
$T_j, ^\circ\text{C}$	-60...+125							

MAXIMUM ALLOWABLE RATINGS

Symbols and parameters		Units	Values	Test conditions	
ON-STATE					
I_{TAV}	Maximum allowable mean on-state current	A	1000 1394	$T_c=99\text{ }^{\circ}\text{C}$, Double side cooled $T_c=85\text{ }^{\circ}\text{C}$, Double side cooled 180° half-sine wave; 50 Hz	
I_{TRMS}	RMS on-state current	A	1570	$T_c=99\text{ }^{\circ}\text{C}$, Double side cooled 180° half-sine wave; 50 Hz	
I_{TSM}	Surge on-state current	kA	30.0 35.0	$T_j=T_{j\text{ max}}$ $T_j=25\text{ }^{\circ}\text{C}$	180° half-sine wave; $t_p=10\text{ ms}$; single pulse; $V_D=V_R=0\text{ V}$; Gate pulse: $I_G=2\text{ A}$; $t_{GP}=50\text{ }\mu\text{s}$; $di_G/dt\geq 1\text{ A}/\mu\text{s}$
			32.0 37.0	$T_j=T_{j\text{ max}}$ $T_j=25\text{ }^{\circ}\text{C}$	180° half-sine wave; $t_p=8.3\text{ ms}$; single pulse; $V_D=V_R=0\text{ V}$; Gate pulse: $I_G=2\text{ A}$; $t_{GP}=50\text{ }\mu\text{s}$; $di_G/dt\geq 1\text{ A}/\mu\text{s}$
I^2t	Safety factor	$A^2s\cdot 10^3$	4500 6100	$T_j=T_{j\text{ max}}$ $T_j=25\text{ }^{\circ}\text{C}$	180° half-sine wave; $t_p=10\text{ ms}$; single pulse; $V_D=V_R=0\text{ V}$; Gate pulse: $I_G=2\text{ A}$; $t_{GP}=50\text{ }\mu\text{s}$; $di_G/dt\geq 1\text{ A}/\mu\text{s}$
			4200 5600	$T_j=T_{j\text{ max}}$ $T_j=25\text{ }^{\circ}\text{C}$	180° half-sine wave; $t_p=8.3\text{ ms}$; single pulse; $V_D=V_R=0\text{ V}$; Gate pulse: $I_G=2\text{ A}$; $t_{GP}=50\text{ }\mu\text{s}$; $di_G/dt\geq 1\text{ A}/\mu\text{s}$
BLOCKING					
V_{DRM}, V_{RRM}	Repetitive peak off-state and Repetitive peak reverse voltages	V	1000...1800	$T_{j\text{ min}} < T_j < T_{j\text{ max}}$; 180° half-sine wave; 50 Hz; Gate open	
V_{DSM}, V_{RSM}	Non-repetitive peak off-state and Non-repetitive peak reverse voltages	V	1100...1900	$T_{j\text{ min}} < T_j < T_{j\text{ max}}$; 180° half-sine wave; single pulse; Gate open	
V_D, V_R	Direct off-state and Direct reverse voltages	V	$0.6\cdot V_{DRM}$ $0.6\cdot V_{RRM}$	$T_j=T_{j\text{ max}}$; Gate open	

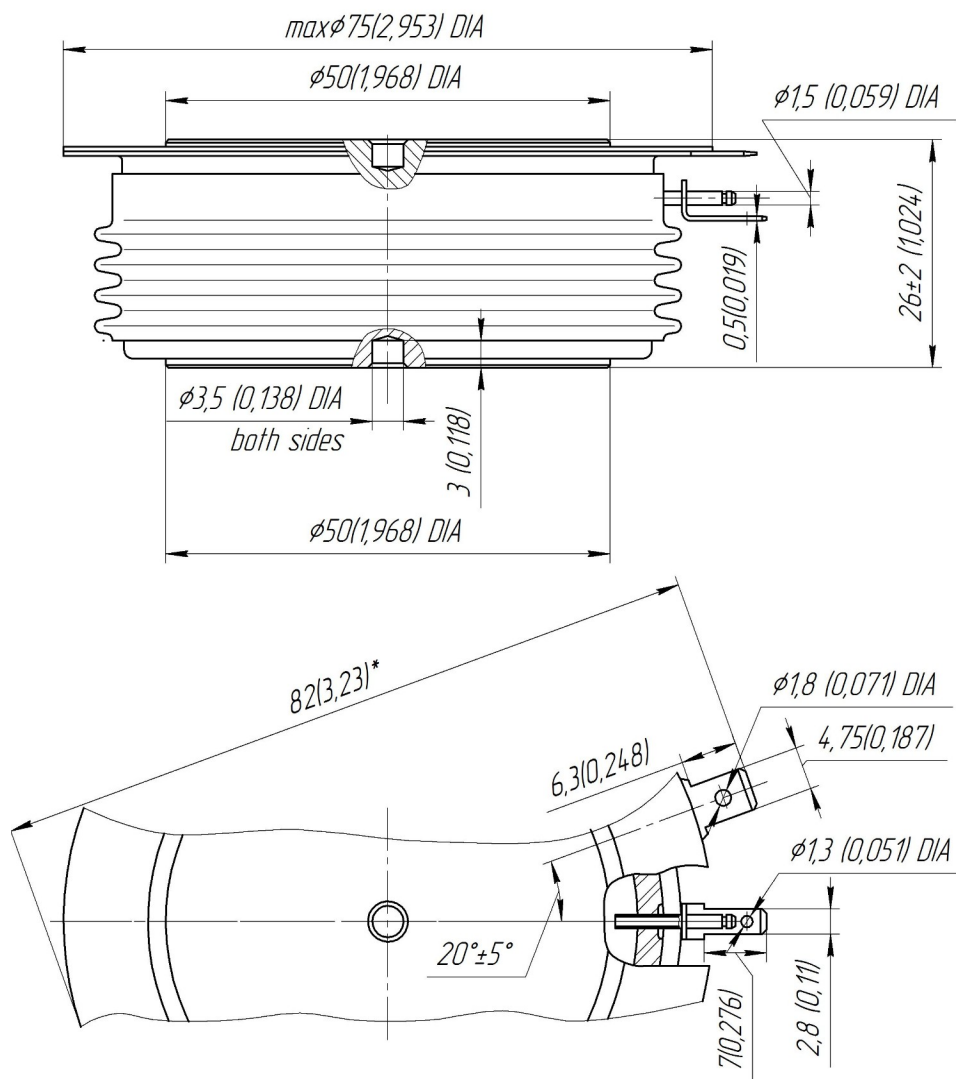
TRIGGERING				
I_{FGM}	Peak forward gate current	A	8	$T_j = T_{j\max}$
V_{RGM}	Peak reverse gate voltage	V	5	
P_G	Gate power dissipation	W	4	$T_j = T_{j\max}$ for DC gate current
SWITCHING				
$(di_T/dt)_{crit}$	Critical rate of rise of on-state current non-repetitive ($f=1$ Hz)	A/ μ s	2000	$T_j = T_{j\max}$; $V_D = 0.67 \cdot V_{DRM}$; $I_{TM} = 4000$ A; Gate pulse: $I_G = 2$ A; $t_{GP} = 50$ μ s; $di_G/dt \geq 2$ A/ μ s
THERMAL				
T_{stg}	Storage temperature	$^{\circ}$ C	-60...+50	
T_j	Operating junction temperature	$^{\circ}$ C	-60...+125	
MECHANICAL				
F	Mounting force	kN	24.0...28.0	
a	Acceleration	m/s ²	50	Device clamped

CHARACTERISTICS

Symbols and parameters		Units	Values	Conditions	
ON-STATE					
V _{TM}	Peak on-state voltage, max	V	1.50	T _j =25 °C; I _{TM} =3140 A	
V _{T(TO)}	On-state threshold voltage, max	V	0.948	T _j =T _{j max} ;	
r _T	On-state slope resistance, max	mΩ	0.189	0.5 π I _{TAV} < I _T < 1.5 π I _{TAV}	
I _L	Latching current, max	mA	1500	T _j =25 °C; V _D =12 V; Gate pulse: I _G =2 A; t _{GP} =50 μs; di _G /dt≥1 A/μs	
I _H	Holding current, max	mA	300	T _j =25 °C; V _D =12 V; Gate open	
BLOCKING					
I _{DRM} , I _{RRM}	Repetitive peak off-state and Repetitive peak reverse currents, max	mA	150	T _j =T _{j max} ; V _D =V _{DRM} ; V _R =V _{RRM}	
(dv _D /dt) _{crit}	Critical rate of rise of off-state voltage ¹⁾ , min	V/μs	200, 320, 500, 1000, 1600, 2000, 2500	T _j =T _{j max} ; V _D =0.67·V _{DRM} ; Gate open	
TRIGGERING					
V _{GT}	Gate trigger direct voltage, max	V	3.00 2.50 1.50	T _j = T _{j min} T _j =25 °C T _j = T _{j max}	V _D =12 V; I _D =3 A; Direct gate current
I _{GT}	Gate trigger direct current, max	mA	400 250 150	T _j = T _{j min} T _j = 25 °C T _j = T _{j max}	
V _{GD}	Gate non-trigger direct voltage, min	V	0.45	T _j =T _{j max} ; V _D =0.67·V _{DRM} ;	
I _{GD}	Gate non-trigger direct current, min	mA	50.00	Direct gate current	
SWITCHING					
t _{gd}	Delay time	μs	0.75	T _j =25 °C; V _D =1000 V; I _{TM} =I _{TAV} ; di/dt=200 A/μs;	
t _{gt}	Turn-on time, max	μs	4.00	Gate pulse: I _G =2 A; V _G =20 V; t _{GP} =50 μs; di _G /dt=2 A/μs	
t _q	Turn-off time ²⁾ , max	μs	200, 250, 320, 400, 500	dv _D /dt=50 V/μs; T _j =T _{j max} ; I _{TM} = I _{TAV} ; di _R /dt=-10 A/μs; V _R =100V; V _D =0.67·V _{DRM}	
Q _{rr}	Recovered charge, max	μC	2700	T _j =T _{j max} ; I _{TM} = I _{TAV} ;	
t _{rr}	Reverse recovery time, max	μs	30	di _R /dt=-10 A/μs;	
I _{rr}	Reverse recovery current, max	A	180	V _R =100 V;	

THERMAL					
R _{thjc}	Thermal resistance, junction to case, max	°C/W	0.0180	Direct current	Double side cooled
R _{thjc-A}			0.0396		Anode side cooled
R _{thjc-K}			0.0324		Cathode side cooled
R _{thck}	Thermal resistance, case to heatsink, max	°C/W	0.0040	Direct current	
MECHANICAL					
m	Weight, max	g	500		
D _s	Surface creepage distance	mm (inch)	30.38 (1.196)		
D _a	Air strike distance	mm (inch)	18.05 (0.710)		

PART NUMBERING GUIDE							NOTES																						
T	253	1000	18	A2	E2	N	1) Critical rate of rise of off-state voltage																						
1	2	3	4	5	6	7	<table><tr><td>Symbol of Group</td><td>P2</td><td>K2</td><td>E2</td><td>A2</td><td>T1</td><td>P1</td><td>M1</td></tr><tr><td>(dv_D/dt)_{crit}, V/μs</td><td>200</td><td>320</td><td>500</td><td>1000</td><td>1600</td><td>2000</td><td>2500</td></tr></table>							Symbol of Group	P2	K2	E2	A2	T1	P1	M1	(dv _D /dt) _{crit} , V/μs	200	320	500	1000	1600	2000	2500
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(dv _D /dt) _{crit} , V/μs	200	320	500	1000	1600	2000	2500																						
1. Phase Control Thyristor							2) Turn-off time (dv _D /dt=50 V/μs)																						
2. Design version							<table><tr><td>Symbol of Group</td><td>P2</td><td>M2</td><td>K2</td><td>H2</td><td>E2</td></tr><tr><td>t_q, μs</td><td>200</td><td>250</td><td>320</td><td>400</td><td>500</td></tr></table>							Symbol of Group	P2	M2	K2	H2	E2	t _q , μs	200	250	320	400	500				
Symbol of Group	P2	M2	K2	H2	E2																								
t _q , μs	200	250	320	400	500																								
3. Mean on-state current, A																													
4. Voltage code																													
5. Critical rate of rise of off-state voltage, V/μs																													
6. Turn-off time (dv _D /dt=50 V/μs)																													
7. Ambient conditions: N – normal; T – tropical																													



All dimensions in millimeters (inches)

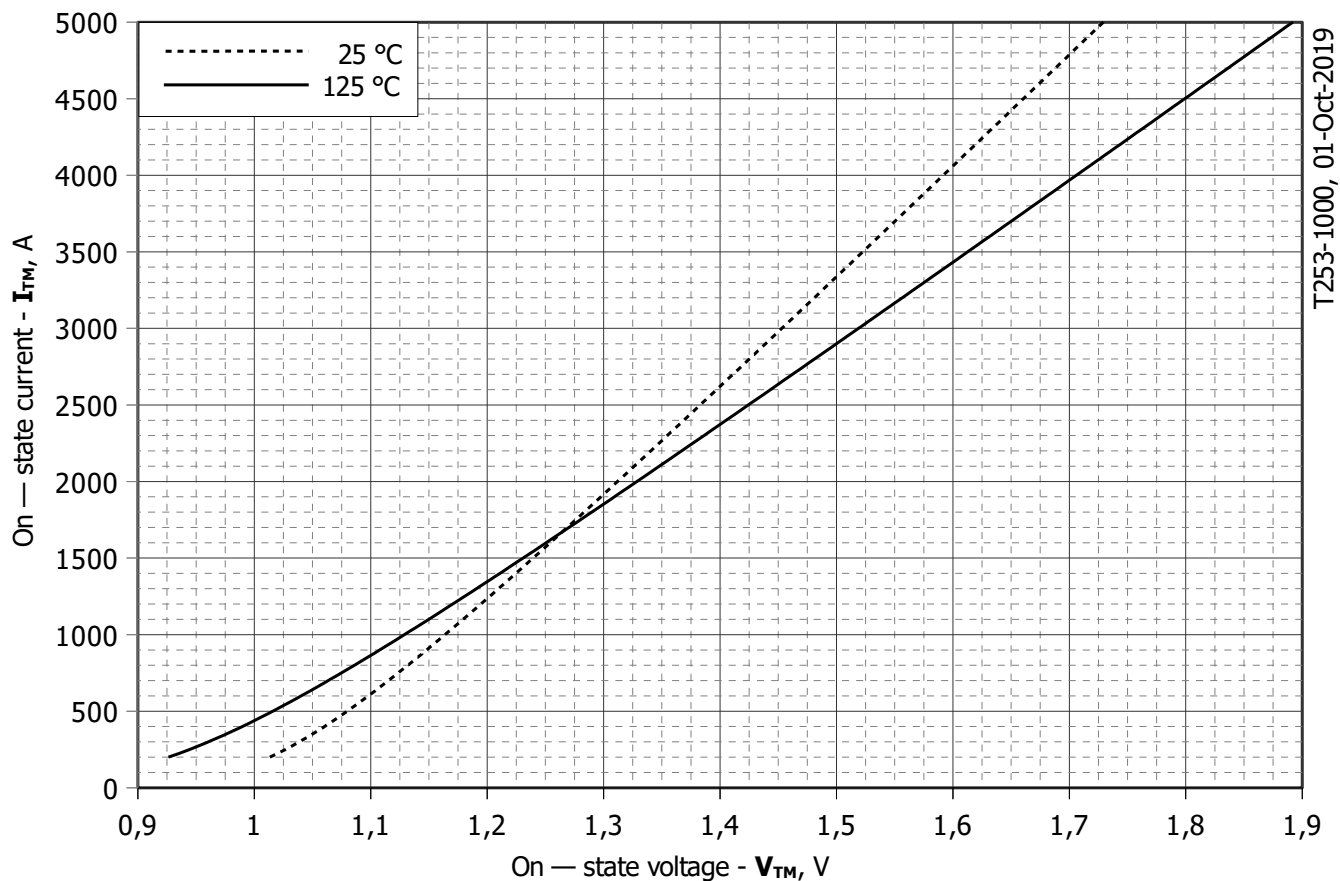


Fig 1 – On-state characteristics of Limit device

Analytical function for On-state characteristic:

$$V_T = A + B \cdot i_T + C \cdot \ln(i_T + 1) + D \cdot \sqrt{i_T}$$

	Coefficients for max curves	
	$T_j = 25^\circ\text{C}$	$T_j = T_{j\text{max}}$
A	0.79350000	0.62414000
B	0.00013927	0.00018985
C	0.04000500	0.05565300
D	-0.00143400	-0.00219830

On-state characteristic model (see Fig. 1)

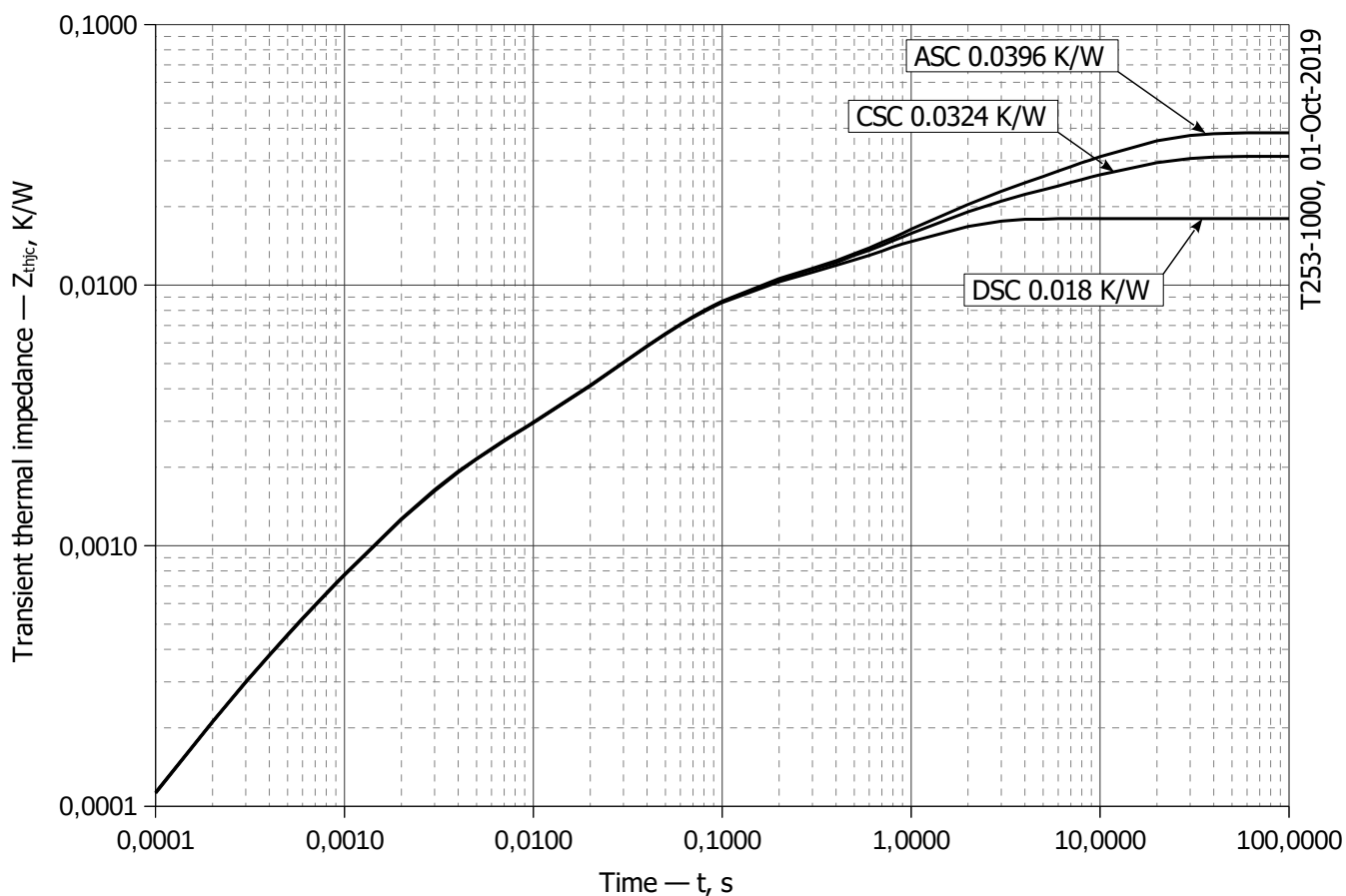


Fig 2 – Transient thermal impedance Z_{thjc} vs. time t

Analytical function for Transient thermal impedance junction to case Z_{thjc} for DC:

$$Z_{thjc} = \sum_{i=1}^n R_i \left(1 - e^{-\frac{t}{\tau_i}} \right)$$

Where $i = 1$ to n , n is the number of terms in the series.

t = Duration of heating pulse in seconds.

Z_{thjc} = Thermal resistance at time t .

R_i = Amplitude of p_{th} term.

τ_i = Time constant of r_{th} term.

DC Double side cooled

i	1	2	3	4	5	6
R_i , K/W	0.009241	0.006037	0.001231	0.001054	0.0003396	0.00009575
τ_i , s	0.9673	0.04967	0.002733	0.07734	0.001638	0.0002248

DC Anode side cooled

i	1	2	3	4	5	6
R_i , K/W	0.01318	0.009281	0.006055	0.001018	0.001535	0.0001182
τ_i , s	9.745	1.028	0.05591	0.03732	0.002468	0.0002687

DC Cathode side cooled

i	1	2	3	4	5	6
R_i , K/W	0.02041	0.009325	0.006949	0.0001252	0.001516	0.0001119
τ_i , s	9.752	1.065	0.05344	0.01407	0.002421	0.0002554

Transient thermal impedance junction to case Z_{thjc} model (see Fig. 2)

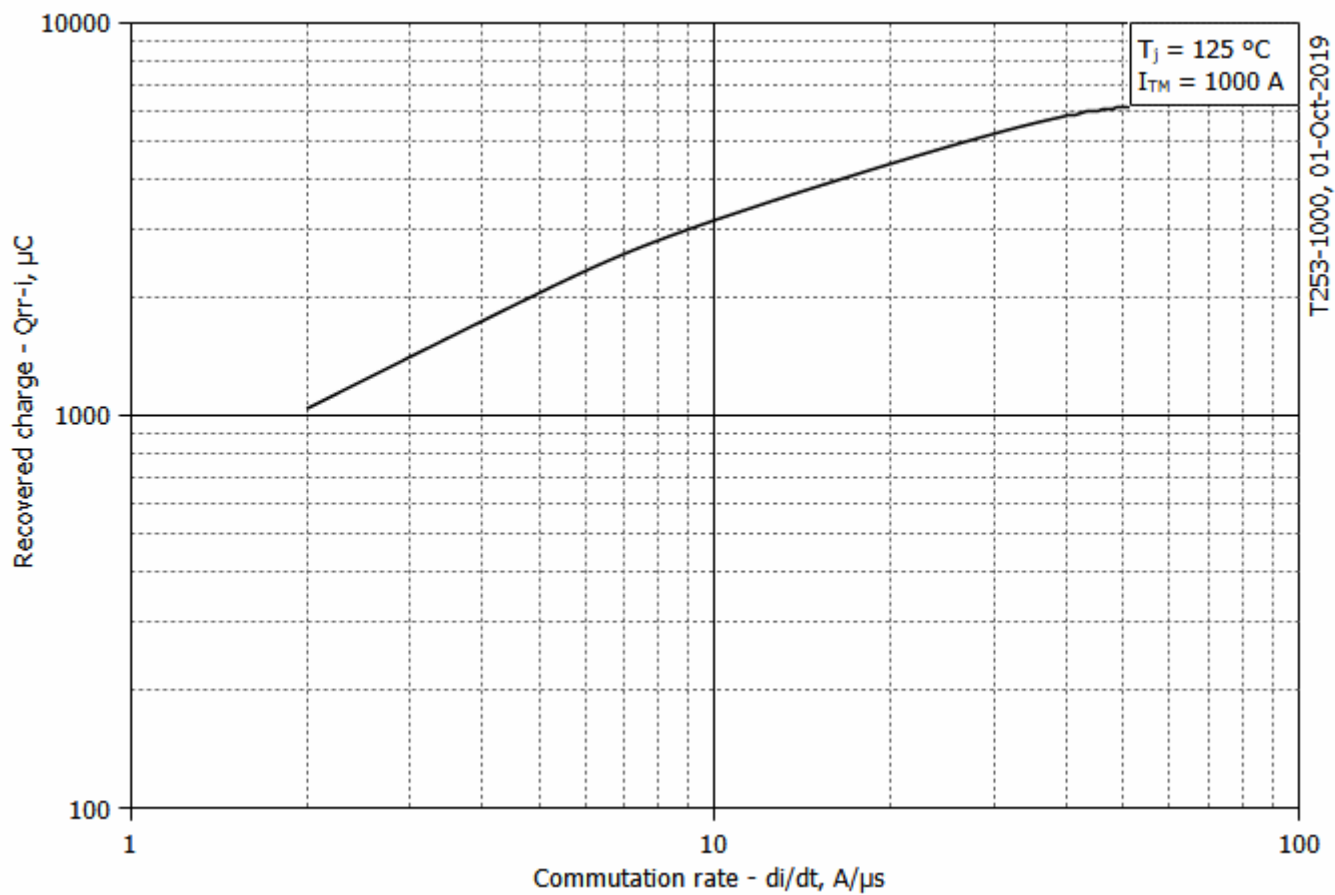


Fig 3 – Maximum recovered charge Q_{rr-i} (integral) vs. commutation rate di_R/dt

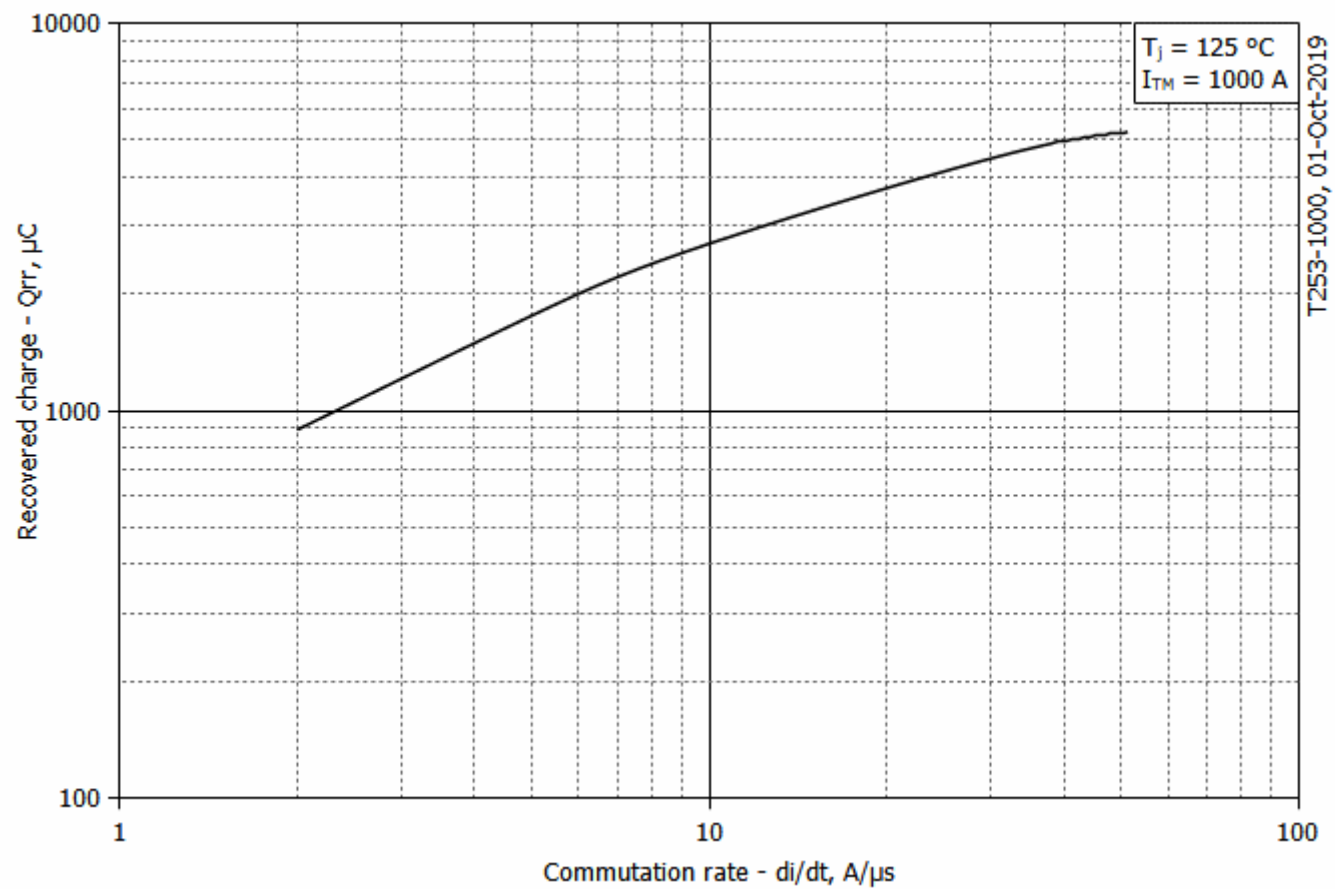


Fig 4 – Maximum recovered charge Q_{rr} vs. commutation rate di_R/dt (25% chord)

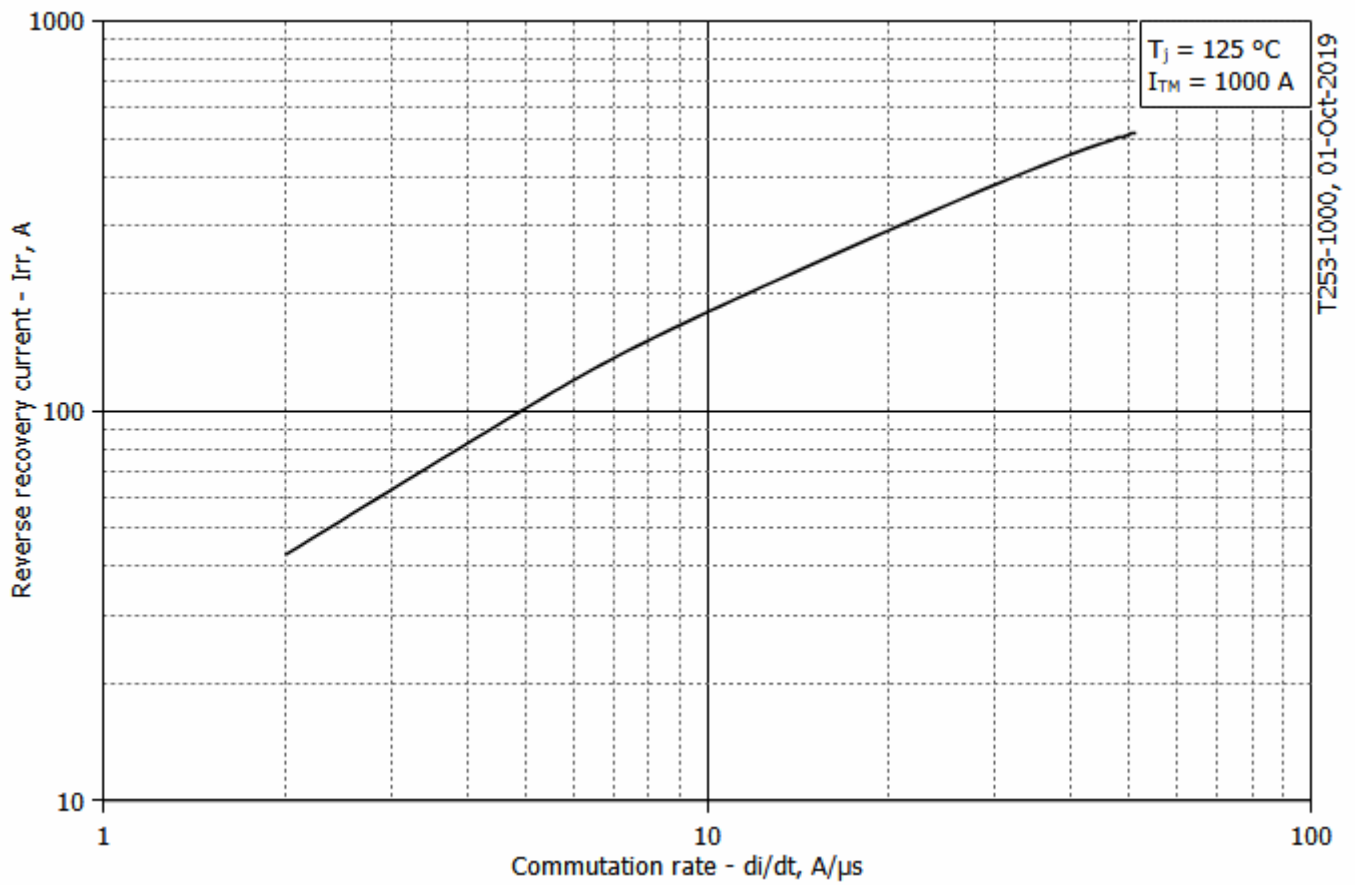


Fig 5 – Maximum reverse recovery current I_{rr} vs. commutation rate di_R/dt

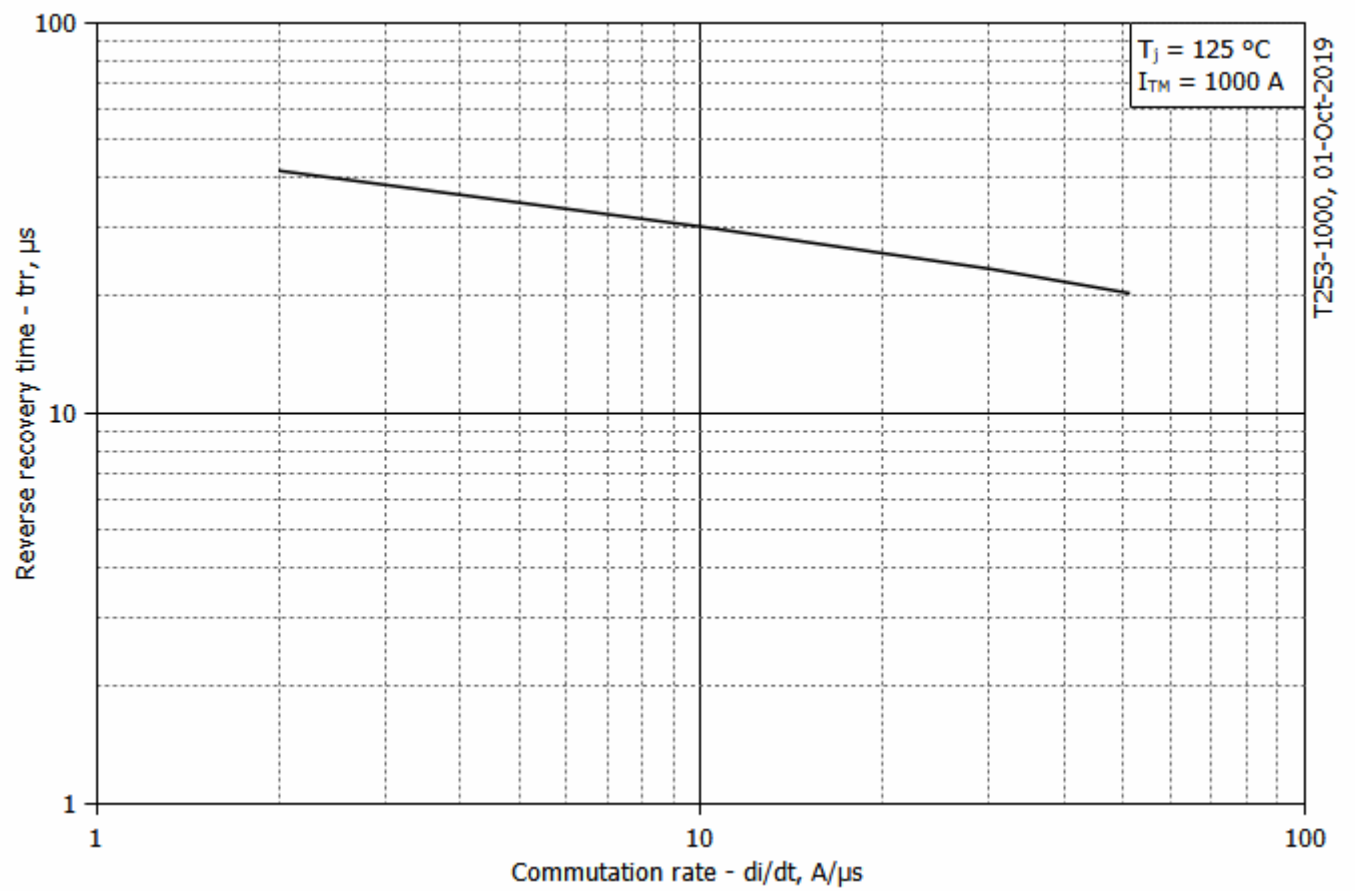
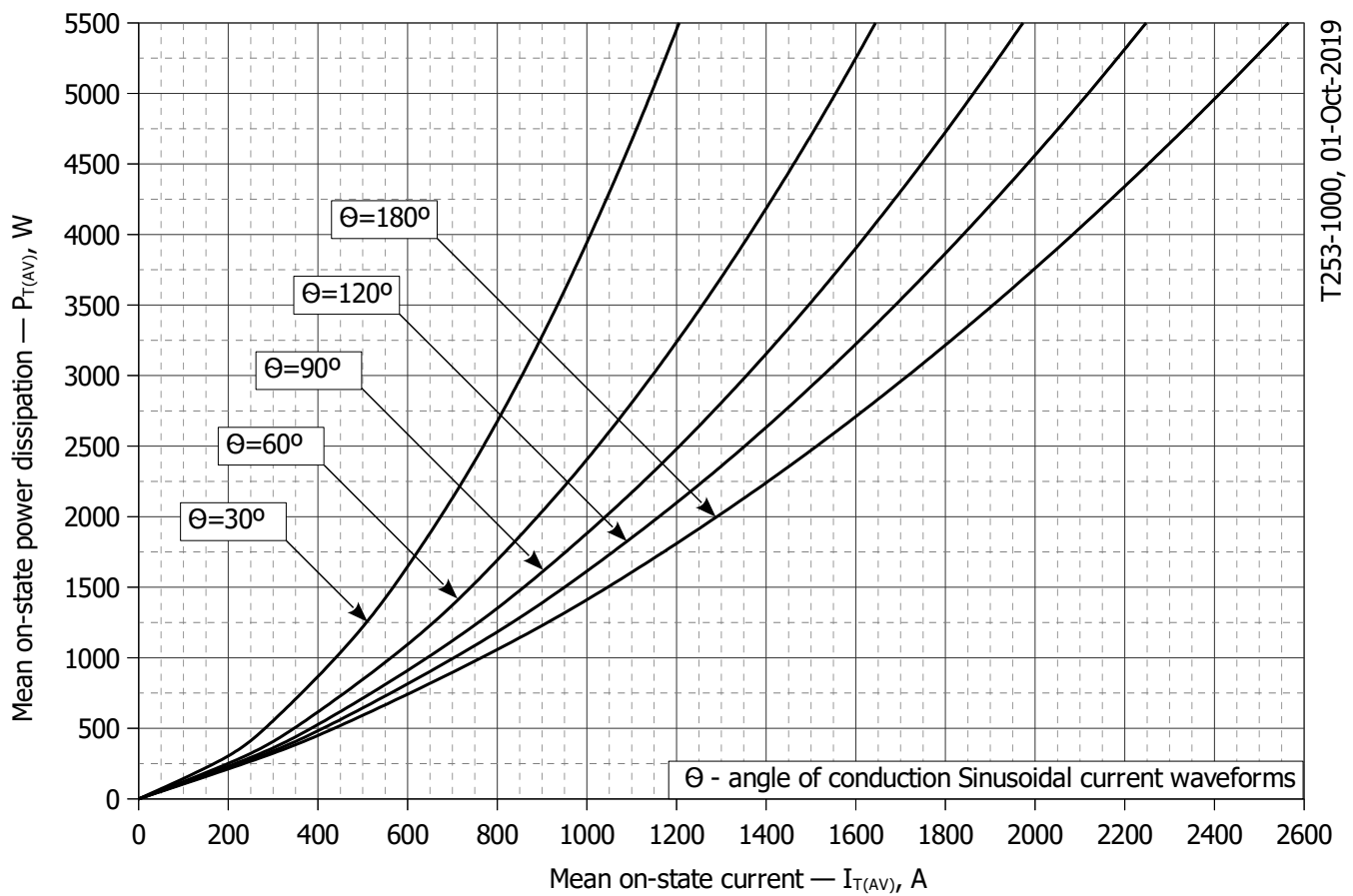
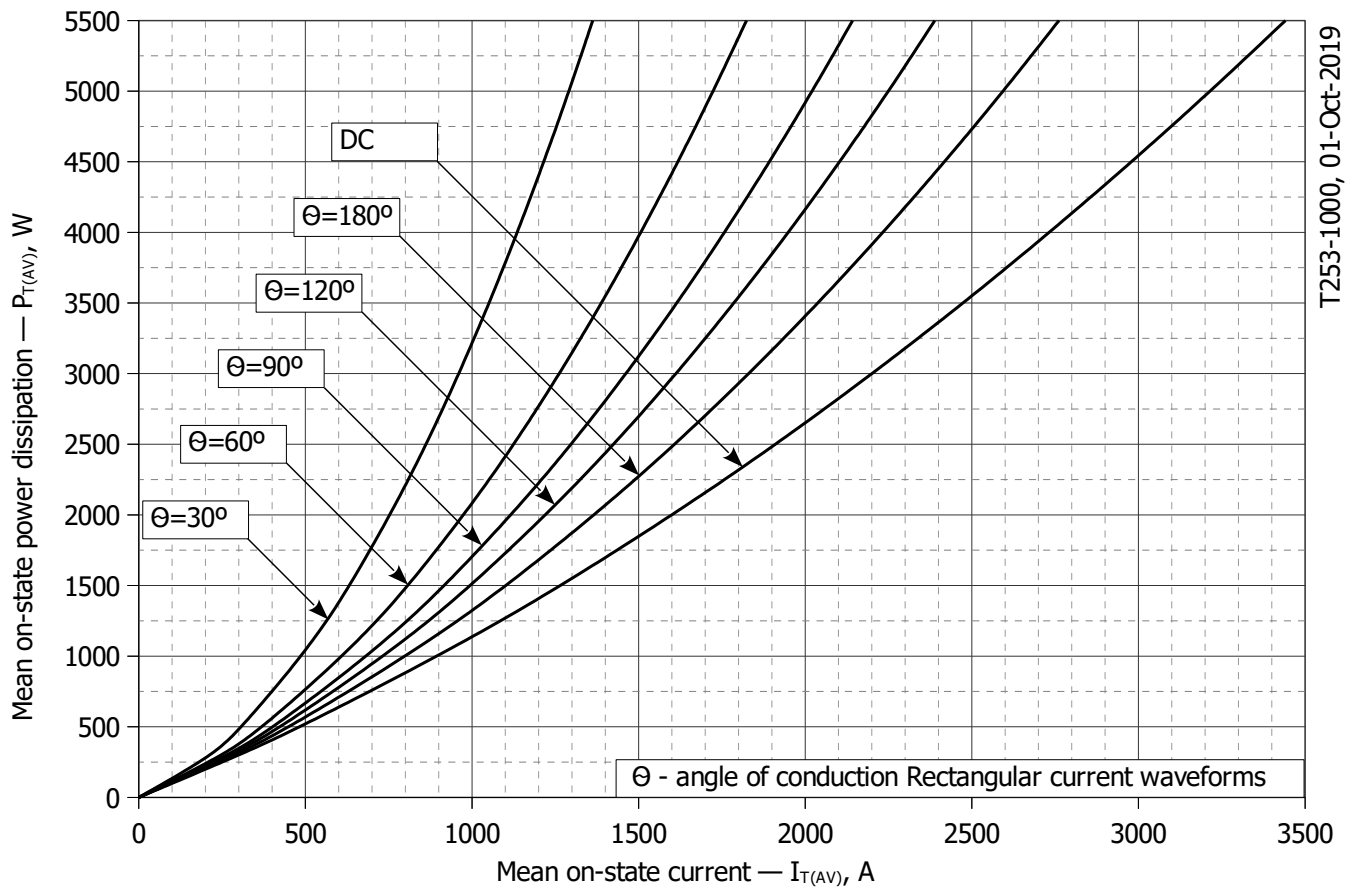


Fig 6 – Maximum recovery time t_{rr} vs. commutation rate di_R/dt (25% chord)



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Fig. 7 - Mean on-state power dissipation P_{TAV} vs. mean on-state current I_{TAV} for sinusoidal current waveforms at different conduction angles ($f=50\text{Hz}$, DSC)



T253-1000, 01-Oct-2019

Fig. 8 - Mean on-state power dissipation P_{TAV} vs. mean on-state current I_{TAV} for rectangular current waveforms at different conduction angles and for DC ($f=50\text{Hz}$, DSC)

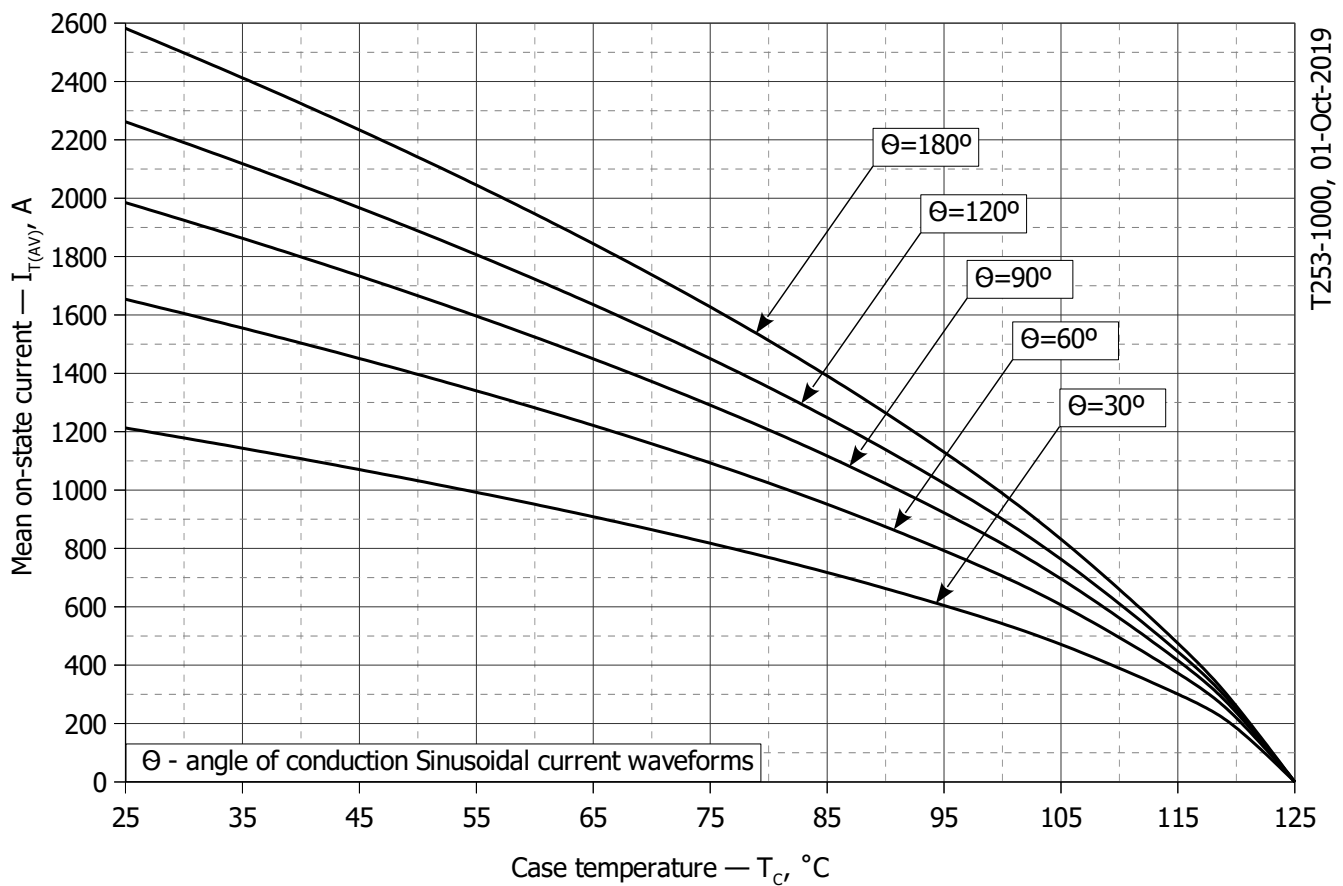


Fig. 9 – Mean on-state current I_{TAV} vs. case temperature T_c for sinusoidal current waveforms at different conduction angles ($f=50\text{Hz}$, DSC)

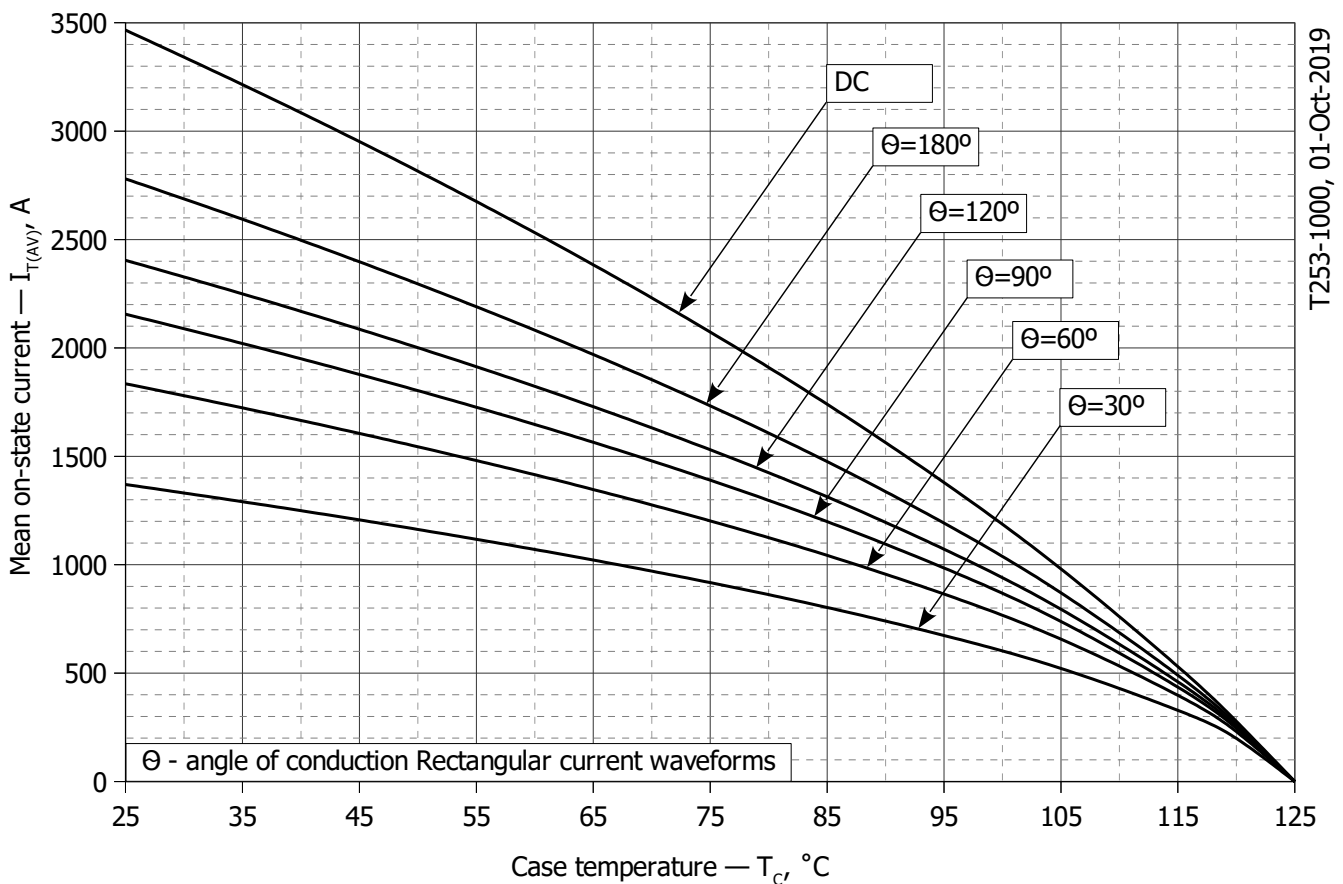


Fig. 10 - Mean on-state current I_{TAV} vs. case temperature T_c for rectangular current waveforms at different conduction angles and for DC ($f=50\text{Hz}$, DSC)

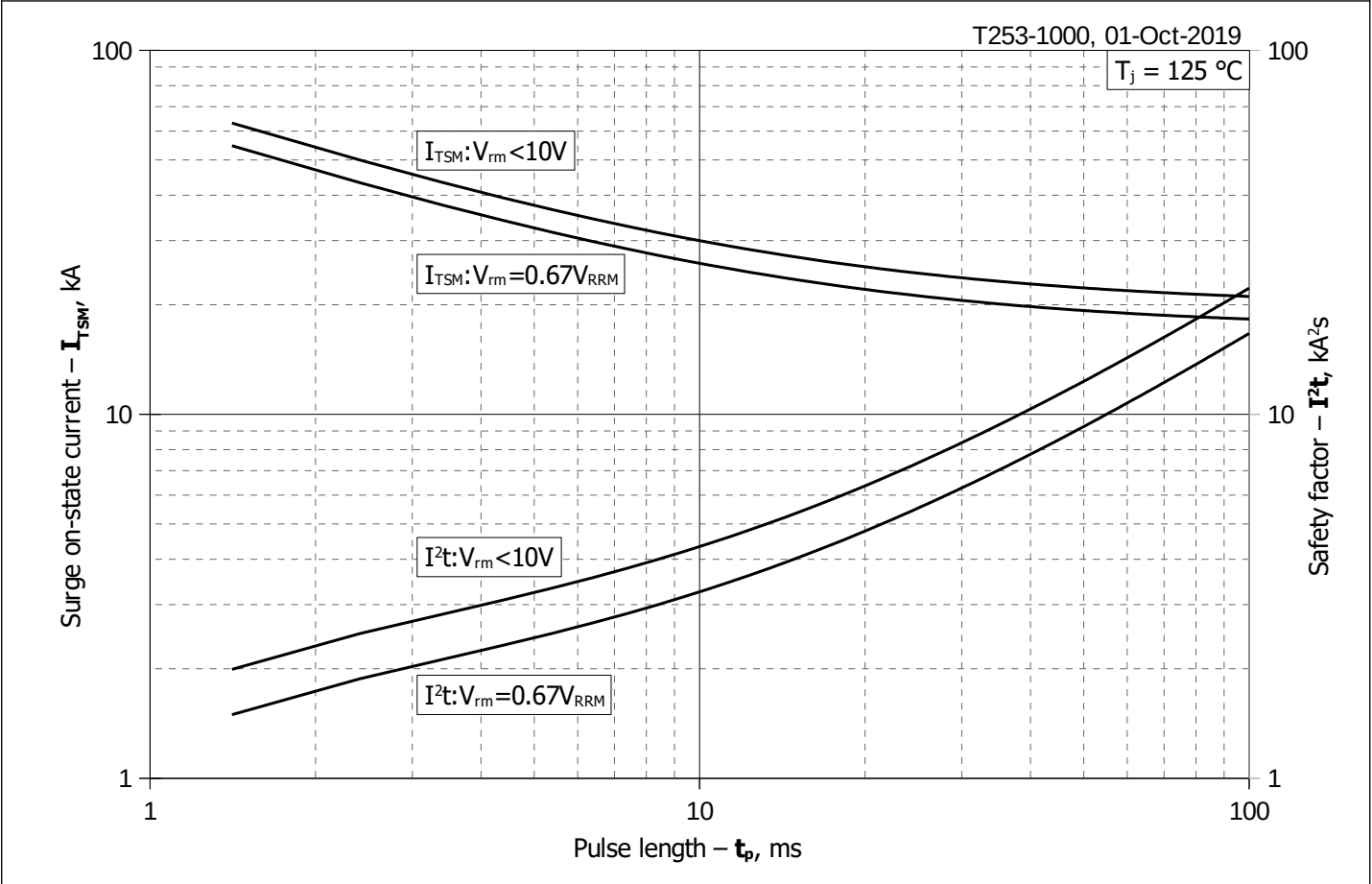


Fig. 11 – Maximum surge on-state current I_{TSM} and safety factor I^2t vs. pulse length t_p

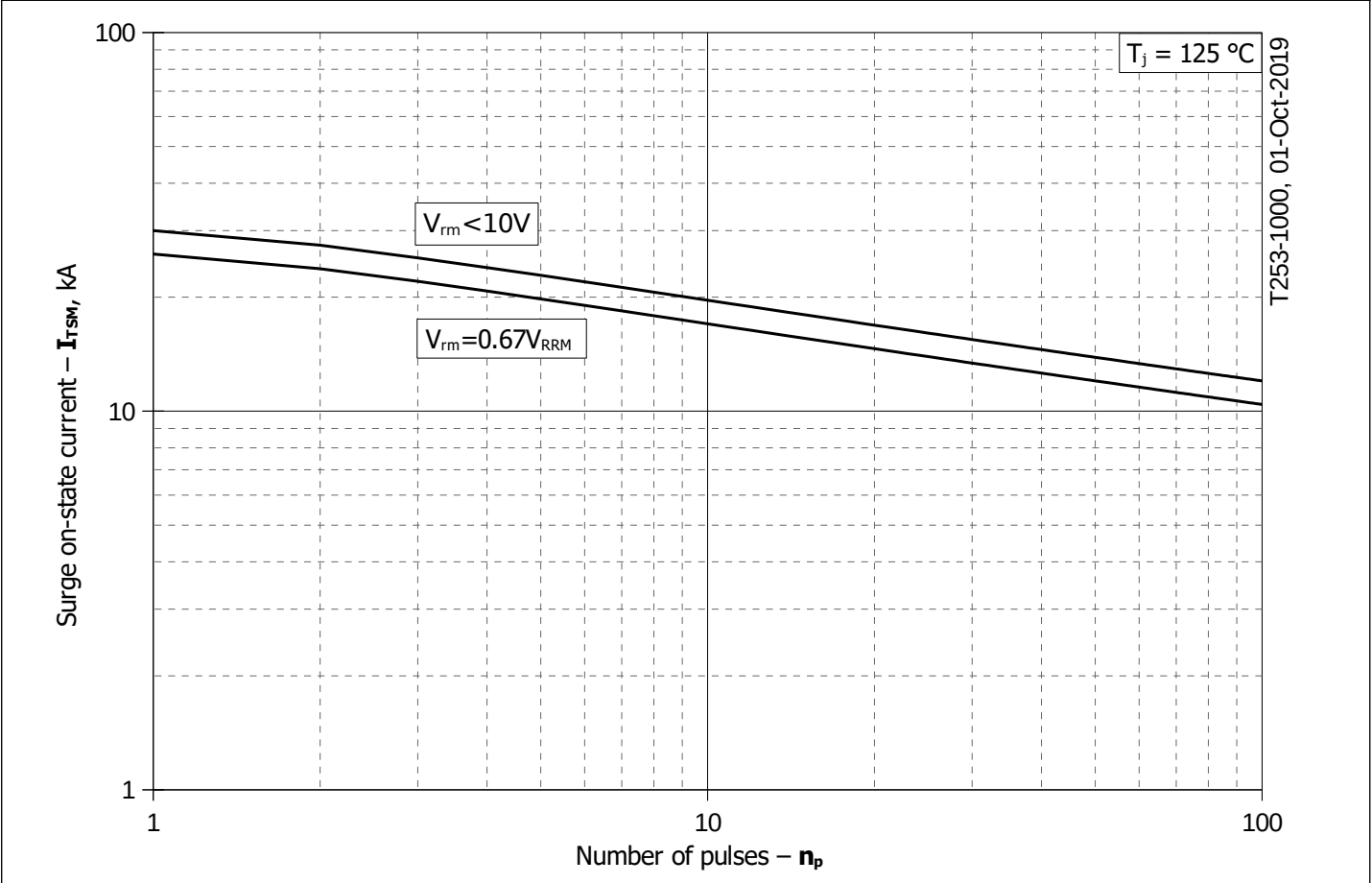


Fig. 12 - Maximum surge on-state current I_{TSM} vs. number of pulses n_p